

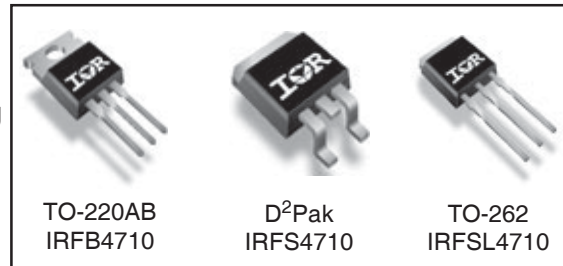
### Applications

- High frequency DC-DC converters
- Motor Control
- Uninterruptible Power Supplies
- Lead-Free

### Benefits

- Low Gate-to-Drain Charge to Reduce Switching Losses
- Fully Characterized Capacitance Including Effective  $C_{OSS}$  to Simplify Design, (See App. Note AN1001)
- Fully Characterized Avalanche Voltage and Current

$V_{DSS}$	$R_{DS(on) max}$	$I_D$
100V	0.014 $\Omega$	75A



### Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	75	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	53	
$I_{DM}$	Pulsed Drain Current ①	300	
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation ②	3.8	W
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	200	
	Linear Derating Factor	1.4	W/ $^\circ\text{C}$
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
dv/dt	Peak Diode Recovery dv/dt ③	8.2	V/ns
$T_J$	Operating Junction and	-55 to + 175	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	
	Mounting torque, 6-32 or M3 screw ④	10 lbf•in (1.1N•m)	

### Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.74	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface ⑤	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient ⑥	—	62	
$R_{\theta JA}$	Junction-to-Ambient ⑦	—	40	

Notes ① through ⑦ are on page 11

www.irf.com

# IRFB/IRFS/IRFL4710PbF

International  
IR Rectifier

## Static @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	100	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.11	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	0.011	0.014	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 45A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	3.5	—	5.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	1.0	μA	V <sub>DS</sub> = 95V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 150°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -20V

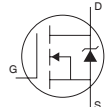
## Dynamic @ T<sub>J</sub> = 25°C (unless otherwise specified)

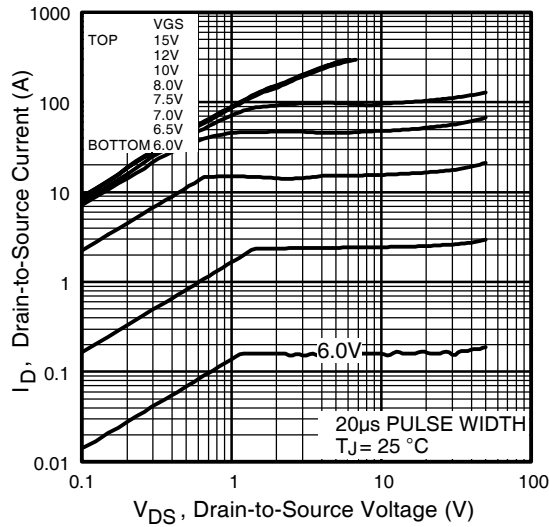
	Parameter	Min.	Typ.	Max.	Units	Conditions
g <sub>fs</sub>	Forward Transconductance	35	—	—	S	V <sub>DS</sub> = 50V, I <sub>D</sub> = 45A
Q <sub>g</sub>	Total Gate Charge	—	110	170	nC	I <sub>D</sub> = 45A
Q <sub>gs</sub>	Gate-to-Source Charge	—	43	—		V <sub>DS</sub> = 50V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	40	—		V <sub>GS</sub> = 10V,
t <sub>d(on)</sub>	Turn-On Delay Time	—	35	—	ns	V <sub>DD</sub> = 50V
t <sub>r</sub>	Rise Time	—	130	—		I <sub>D</sub> = 45A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	41	—		R <sub>G</sub> = 4.5Ω
t <sub>f</sub>	Fall Time	—	38	—		V <sub>GS</sub> = 10V ④
C <sub>iss</sub>	Input Capacitance	—	6160	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	440	—		V <sub>DS</sub> = 25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	250	—		f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	1580	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 1.0V, f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	280	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 80V, f = 1.0MHz
C <sub>oss eff.</sub>	Effective Output Capacitance	—	430	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V to 80V ⑤

## Avalanche Characteristics

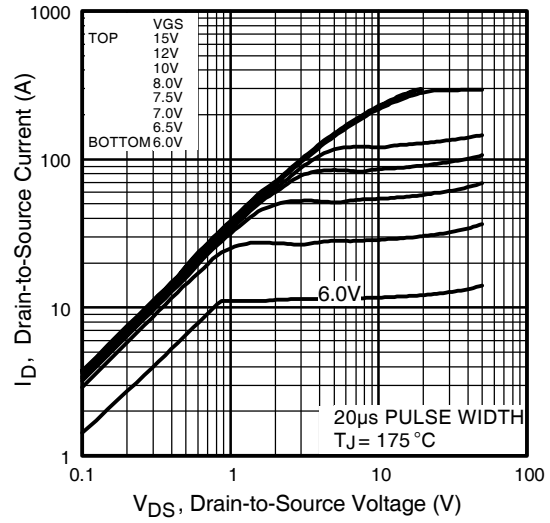
	Parameter	Typ.	Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy②	—	190	mJ
I <sub>AR</sub>	Avalanche Current①	—	45	A
E <sub>AR</sub>	Repetitive Avalanche Energy①	—	20	mJ

## Diode Characteristics

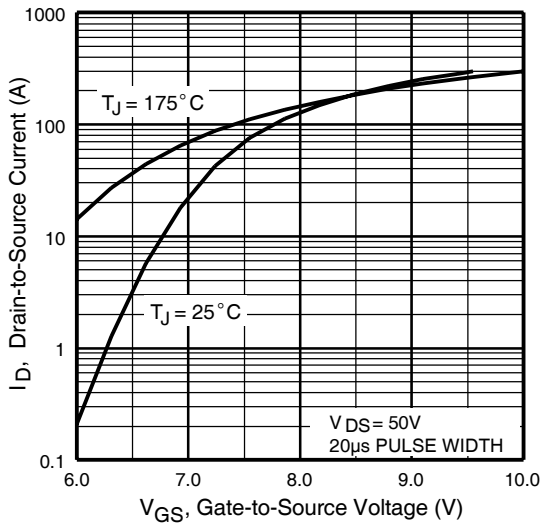
	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	75	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①⑥	—	—	300		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 45A, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	74	110	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 45A
Q <sub>rr</sub>	Reverse Recovery Charge	—	180	260	nC	di/dt = 100A/μs ④
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				



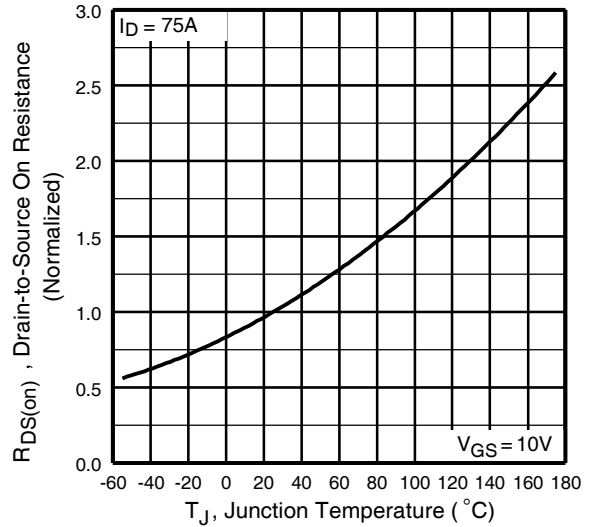
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics

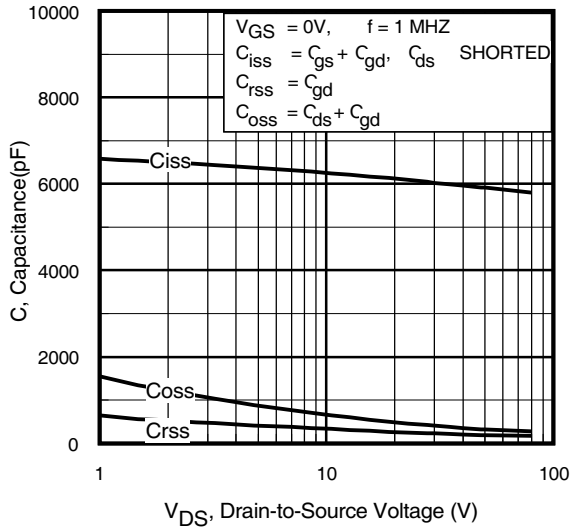


**Fig 3.** Typical Transfer Characteristics

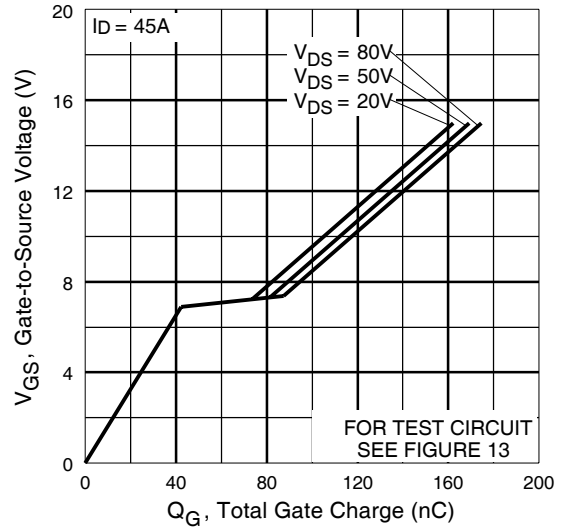


**Fig 4.** Normalized On-Resistance Vs. Temperature

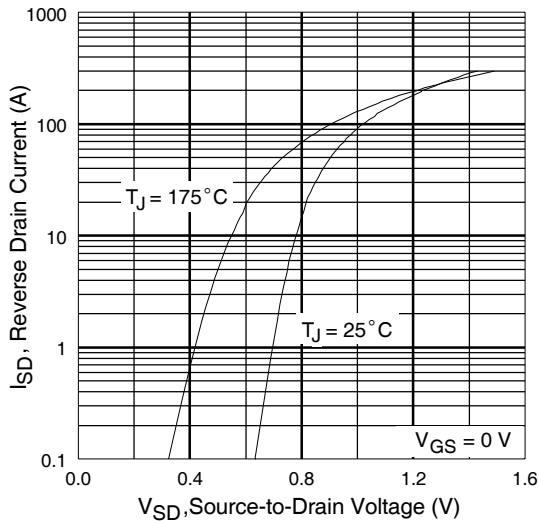
# IRFB/IRFS/IRFL4710PbF



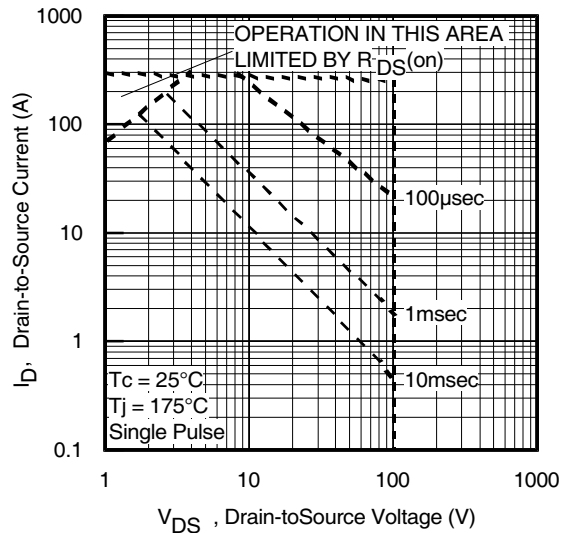
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



**Fig 7.** Typical Source-Drain Diode Forward Voltage



**Fig 8.** Maximum Safe Operating Area

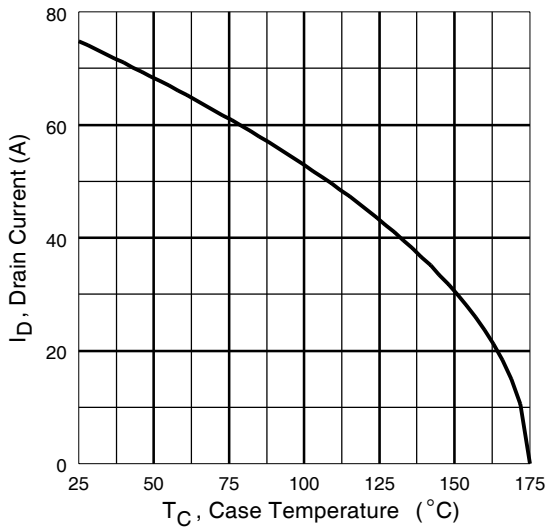


Fig 9. Maximum Drain Current Vs. Case Temperature

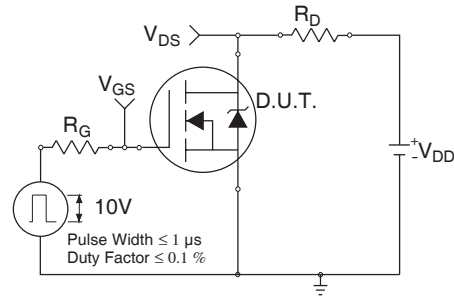


Fig 10a. Switching Time Test Circuit



Fig 10b. Switching Time Waveforms

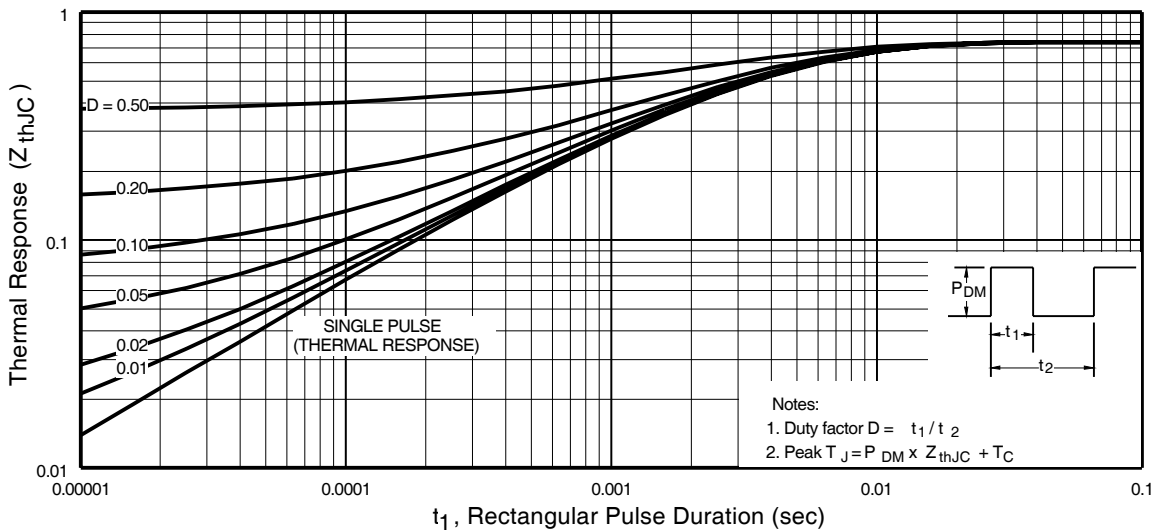
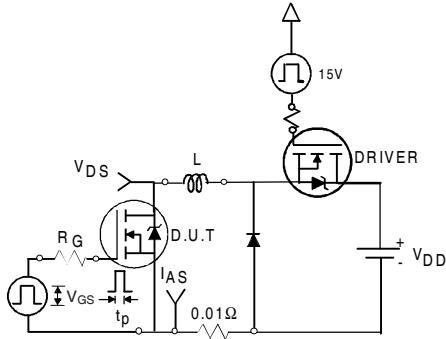


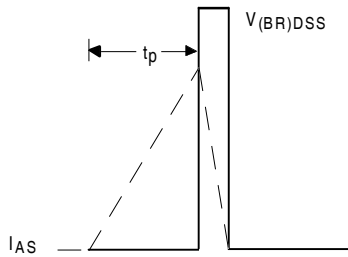
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

# IRFB/IRFS/IRFL4710PbF

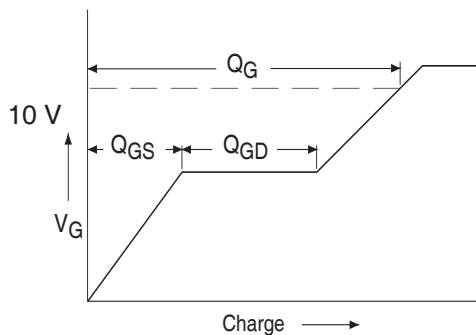
International  
**IR** Rectifier



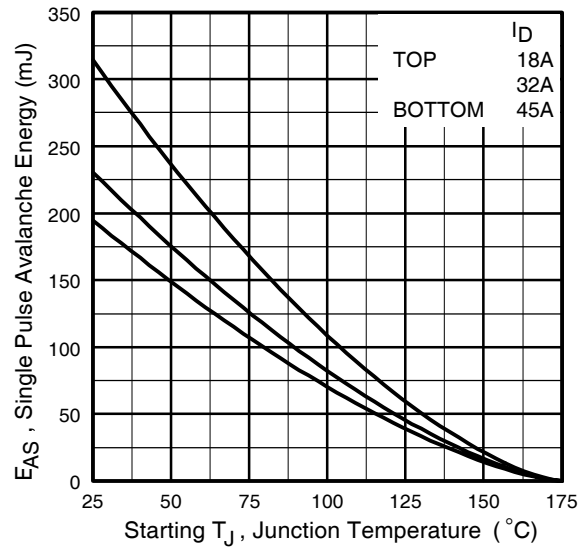
**Fig 12a.** Unclamped Inductive Test Circuit



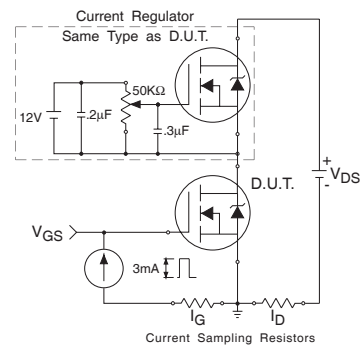
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 13a.** Basic Gate Charge Waveform

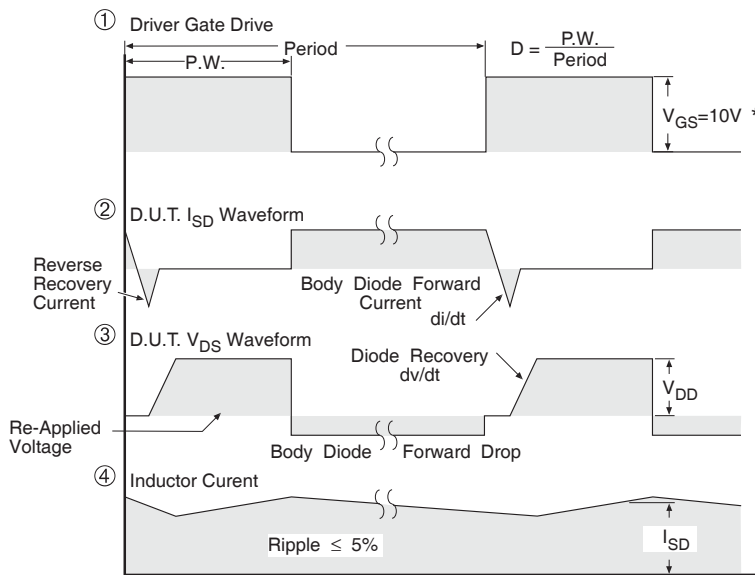
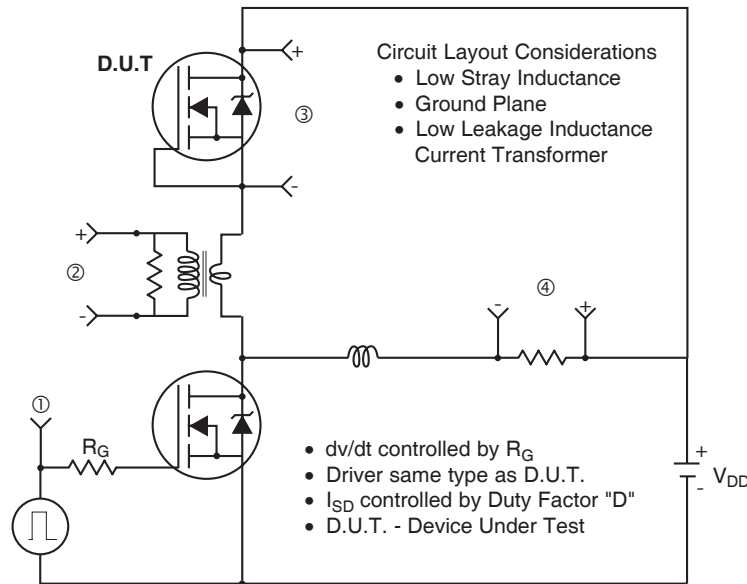


**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



**Fig 13b.** Gate Charge Test Circuit

**Peak Diode Recovery dv/dt Test Circuit**



\*  $V_{GS} = 5V$  for Logic Level Devices

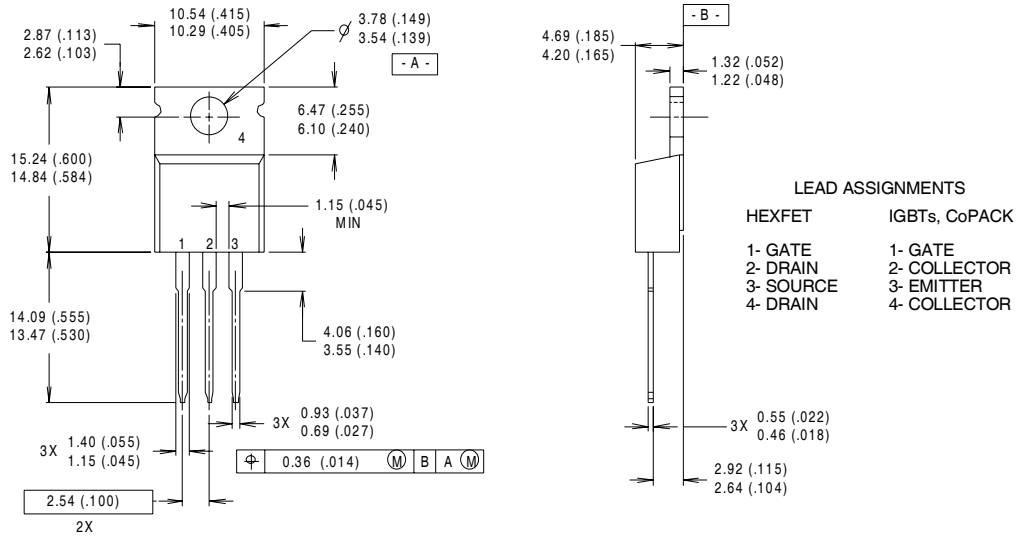
**Fig 14.** For N-Channel HEXFET® Power MOSFETs

# IRFB/IRFS/IRFL4710PbF



## TO-220AB Package Outline

Dimensions are shown in millimeters (inches)

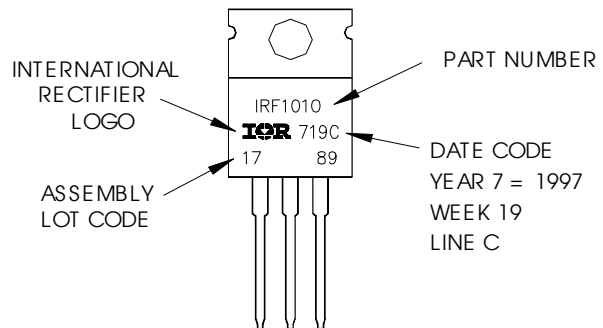


- NOTES:
- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
  - 2 CONTROLLING DIMENSION : INCH
  - 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
  - 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

## TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 1997  
 IN THE ASSEMBLY LINE "C"

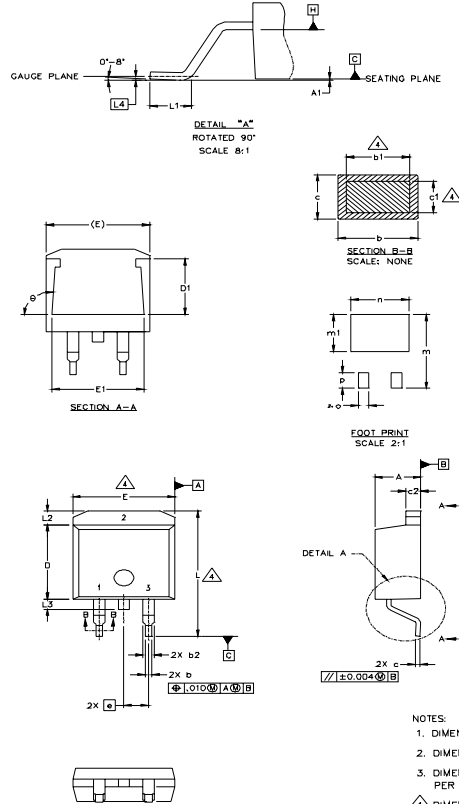
**Note:** "P" in assembly line position indicates "Lead-Free"





## D<sup>2</sup>Pak Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	4
A1		0.127		.005	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	4
c	0.43	0.63	.017	.025	
c1	0.38	0.74	.015	.029	
c2	1.14	1.40	.045	.055	3
D	8.51	9.65	.335	.380	
D1	5.33		.210		3
E	9.65	10.67	.380	.420	
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	14.61	15.88	.575	.625	
L1	1.78	2.79	.070	.110	
L2		1.65		.065	
L3	1.27	1.78	.050	.070	
L4	0.25 BSC		.010 BSC		
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
θ	90°	93°	90°	93°	

### LEAD ASSIGNMENTS

HEXFET	IGBTs, CoPACK	DIODES
1.- GATE	1.- GATE	1.- ANODE *
2.- DRAIN	2.- COLLECTOR	2.- CATHODE
3.- SOURCE	3.- EMITTER	3.- ANODE

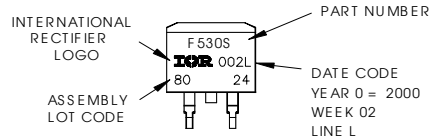
\* PART DEPENDENT.

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
  2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
  3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
  - △ DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
  5. CONTROLLING DIMENSION: INCH.

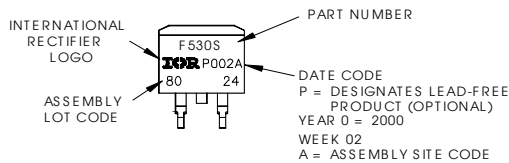
## D<sup>2</sup>Pak Part Marking Information (Lead-Free)

EXAMPLE: THIS IS AN IRF530S WITH LOT CODE 8024 ASSEMBLED ON WW 02, 2000 IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line position indicates "Lead-Free"



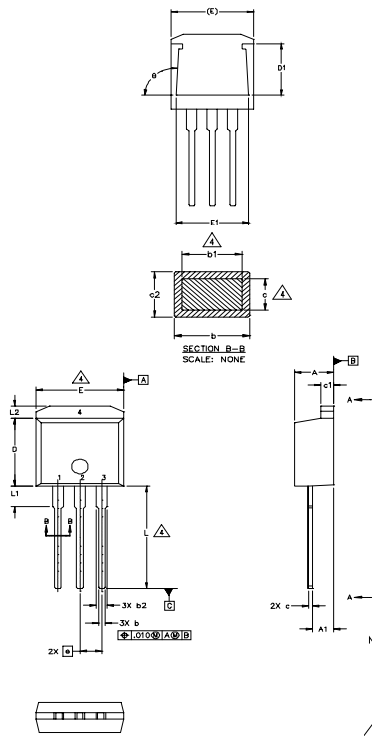
OR



# IRFB/IRFS/IRFL4710PbF

International  
**IR** Rectifier

## TO-262 Package Outline



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.40	.045	.055	
c	0.38	0.63	.015	.025	4
c1	1.14	1.40	.045	.055	
c2	0.43	.063	.017	.029	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	13.46	14.09	.530	.555	
L1	3.56	3.71	.140	.146	
L2		1.65		.065	

### LEAD ASSIGNMENTS

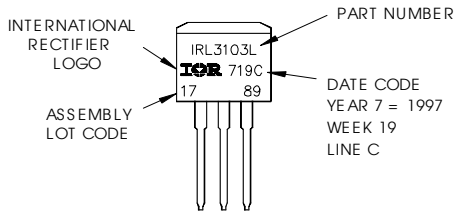
HEXFET	IGBT
1.- GATE	1 - GATE
2.- DRAIN	2 - COLLECTOR
3.- SOURCE	3 - EMITTER
4.- DRAIN	

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
  2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
  3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
  4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
  5. CONTROLLING DIMENSION: INCH.

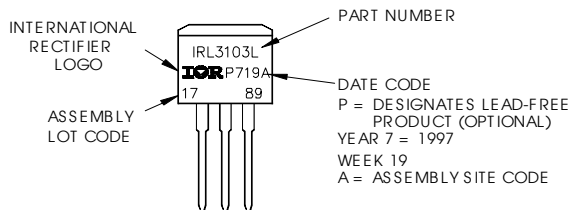
## TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L  
LOT CODE 1789  
ASSEMBLED ON WW 19, 1997  
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead-Free"

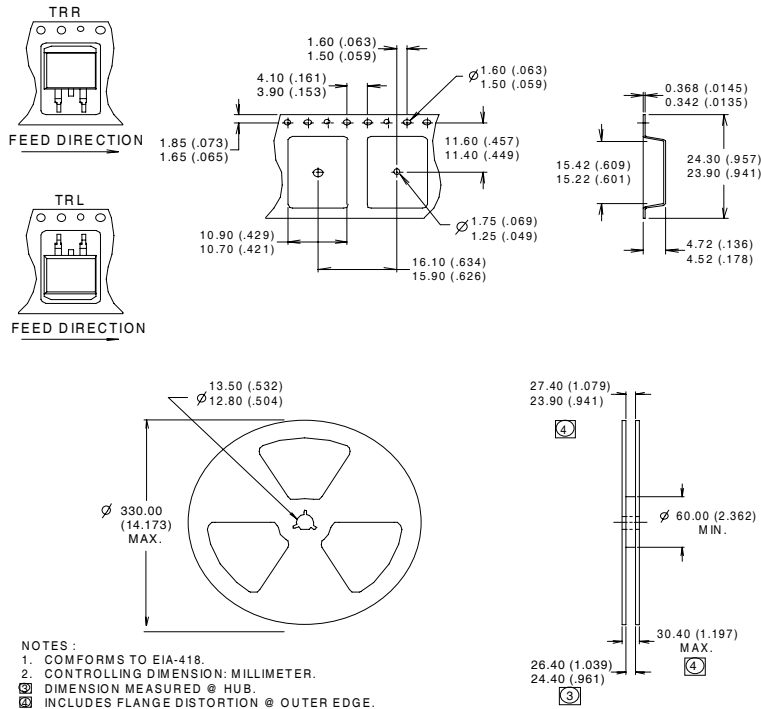


**OR**



## D<sup>2</sup>Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 190\mu\text{H}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 45\text{A}$ ,  $V_{GS} = 10\text{V}$
- ③  $I_{SD} \leq 45\text{A}$ ,  $di/dt \leq 420\text{A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  
 $T_J \leq 175^\circ\text{C}$
- ④ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ⑤  $C_{OSS}$  eff. is a fixed capacitance that gives the same charging time as  $C_{OSS}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$
- ⑥ This is only applied to TO-220AB package
- ⑦ This is applied to D<sup>2</sup>Pak, when mounted on 1" square PCB ( FR-4 or G-10 Material ).  
 For recommended footprint and soldering techniques refer to application note #AN-994.

Data and specifications subject to change without notice.  
 This product has been designed and qualified for the Industrial market.  
 Qualification Standards can be found on IR's Web site.

Note: For the most current drawings please refer to the IR website at:  
<http://www.irf.com/package/>



**Стандарт  
Электрон  
Связь**

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

**Наши контакты:**

**Телефон:** +7 812 627 14 35

**Электронная почта:** [sales@st-electron.ru](mailto:sales@st-electron.ru)

**Адрес:** 198099, Санкт-Петербург,  
Промышленная ул, дом № 19, литера Н,  
помещение 100-Н Офис 331